

APPLICATION NO.

09/691,353

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EXAMINER

30743 7590 12/15/2004
WHITHAM, CURTIS & CHRISTOFFERSON, P.C.
11491 SUNSET HILLS ROAD
SUITE 340
RESTON, VA 20190

FILING DATE

10/18/2000

ART UNIT PAPER NUMBER

NGUYEN, KHIEM D

2823

DATE MAILED: 12/15/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

FIRST NAMED INVENTOR

James W. Adkisson

Advisory Action	Application No.	Applicant(s)
	09/691,353	ADKISSON ET AL.
	Examiner	Art Unit
	Khiem D Nguyen	2823
The MAILING DATE of this communication appears on the cover sheet with the correspondence address		
THE REPLY FILED 08 November 2004 FAILS TO PLACE THIS APPLICATION IN CONDITION FOR ALLOWANCE. Therefore, further action by the applicant is required to avoid abandonment of this application. A proper reply to a final rejection under 37 CFR 1.113 may only be either: (1) a timely filed amendment which places the application in condition for allowance; (2) a timely filed Notice of Appeal (with appeal fee); or (3) a timely filed Request for Continued Examination (RCE) in compliance with 37 CFR 1.114.		
PERIOD FOR REPLY [check either a) or b)]		
a) The period for reply expires <u>3</u> months from the mailing date of the final rejection. b) The period for reply expires on: (1) the mailing date of this Advisory Action or (2) the date set forth in the final rejection, whichever is later. In no		
b)		
1. A Notice of Appeal was filed on Appellant's Brief must be filed within the period set forth in 37 CFR 1.192(a), or any extension thereof (37 CFR 1.191(d)), to avoid dismissal of the appeal.		
2. The proposed amendment(s) will not be entered because:		
(a) ☑ they raise new issues that would require further consideration and/or search (see NOTE below);		
(b) ☐ they raise the issue of new matter (see Note below);		
(c) they are not deemed to place the application in better form for appeal by materially reducing or simplifying the issues for appeal; and/or		
(d) they present additional claims without canceling a corresponding number of finally rejected claims.		
NOTE: See Continuation Sheet.		
3. Applicant's reply has overcome the following rejection(s):		
4. Newly proposed or amended claim(s) would be allowable if submitted in a separate, timely filed amendment canceling the non-allowable claim(s).		
5. ☐ The a) ☐ affidavit, b) ☐ exhibit, or c) ☐ request for reconsideration has been considered but does NOT place the application in condition for allowance because: <u>See Continuation Sheet</u> .		
6. The affidavit or exhibit will NOT be considered because it is not directed SOLELY to issues which were newly raised by the Examiner in the final rejection.		
7. ☑ For purposes of Appeal, the proposed amendment(s) a) ☑ will not be entered or b) ☐ will be entered and an explanation of how the new or amended claims would be rejected is provided below or appended.		
The status of the claim(s) is (or will be) as follows:		
Claim(s) allowed: none.		
Claim(s) objected to: none.		
Claim(s) rejected: <u>1 and 14-30</u> .		
Claim(s) withdrawn from consideration: none.		
8. The drawing correction filed on is a) approved or b) disapproved by the Examiner.		
9. ☐ Note the attached Information Disclosure Statement(s)(PTO-1449) Paper No(s)		
10. Other:		W. DAVID COLEMAN PRIMARY EXAMINER

Continuation Sheet (PTOL-303) 009/691,353

Application No.

Continuation of 2. NOTE: The proposed amendment changing the scope of independent claims 1 and 24 (i.e., "the layer being able to support epitaxial growth on the side surfaces") raised new issues requiring further consideration and new search.

Continuation of 5. does NOT place the application in condition for allowance because: Applicants contend that Doyle does not perform epitaxial growth, and in fact teaches away from the use of epitaxial growth by describing nitride layers, which are amorphous dielectrics and not semiconductor crystals.

In response to Applicants' contention that Doyle does not perform epitaxial growth, Examiner respectfully disagrees. Applicants are directed to page 3, paragraphs [0052]-[0054] and FIGS. 5-7, where Doyle discloses that the substrate is made by providing a silicon on insulator substrate or comprises monocrystalline silicon and wherein the plurality of channels comprises monocrystalline silicon channels. Although, Doyle does not explicitly teach or suggest perform epitaxial growth, it is note that the features upon which applicant relies (i.e., "the layer being able to support epitaxial growth on the side surfaces") are not recited in the rejected claims. Thus, Applicants' argument relies on the proposed amendment which has not been entered. Therefore, Applicants' argument is moot. For this reason, Examiner holds the rejection proper.